

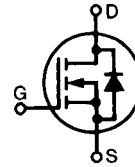
HiPerFET™ Power MOSFETs

ISOPLUS247™

IXFR 26N50
IXFR 24N50

(Electrically Isolated Back Surface)

N-Channel Enhancement Mode
High dV/dt , Low t_{rr} , HDMOS™ Family

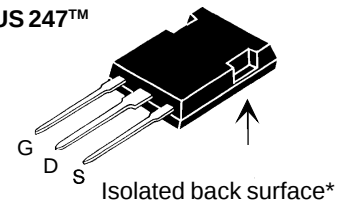


V_{DSS}	I_{D25}	$R_{DS(on)}$
500 V	24 A	0.20 Ω
500 V	22 A	0.23 Ω

$t_{rr} \leq 250$ ns

Symbol	Test Conditions	Maximum Ratings		
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	500	V	
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1$ M Ω	500	V	
V_{GS}	Continuous	± 20	V	
V_{GSM}	Transient	± 30	V	
I_{D25}	$T_C = 25^\circ\text{C}$	26N50 26 24N50 24	A	
I_{DM}	$T_C = 25^\circ\text{C}$, Pulse width limited by T_{JM}	26N50 104 24N50 96	A	
I_{AR}	$T_C = 25^\circ\text{C}$	26N50 26 24N50 24	A	
E_{AR}	$T_C = 25^\circ\text{C}$	30	mJ	
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100$ A/ μs , $V_{DD} \leq V_{DSS}$ $T_J \leq 150^\circ\text{C}$, $R_G = 2$ Ω	5	V/ns	
P_D	$T_C = 25^\circ\text{C}$	250	W	
T_J		-55 ... +150	$^\circ\text{C}$	
T_{JM}		150	$^\circ\text{C}$	
T_{stg}		-55 ... +150	$^\circ\text{C}$	
T_L	1.6 mm (0.062 in.) from case for 10 s	300	$^\circ\text{C}$	
V_{ISOL}	50/60 Hz, RMS $t = 1$ minute leads-to-tab	2500	V~	
Weight		6	g	

ISOPLUS 247™



G = Gate D = Drain
S = Source

* Patent pending

Features

- Silicon chip on Direct-Copper-Bond substrate
- High power dissipation
- Isolated mounting surface
- 2500V electrical isolation
- Low drain to tab capacitance(<50pF)
- Low $R_{DS(on)}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- Unclamped Inductive Switching (UIS) rated
- Fast intrinsic Rectifier

Applications

- DC-DC converters
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- AC motor control

Advantages

- Easy assembly
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_{DSS}	$V_{GS} = 0$ V, $I_D = 250$ μA	500		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 4$ mA	2		V
I_{GSS}	$V_{GS} = \pm 20$ V _{DC} , $V_{DS} = 0$			± 100 nA
I_{DSS}	$V_{DS} = 0.8 \cdot V_{DSS}$ $V_{GS} = 0$ V	$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$		200 μA 1 mA
$R_{DS(on)}$	$V_{GS} = 10$ V, $I_D = I_T$ Notes 1 & 2	26N50 24N50		0.20 Ω 0.23 Ω

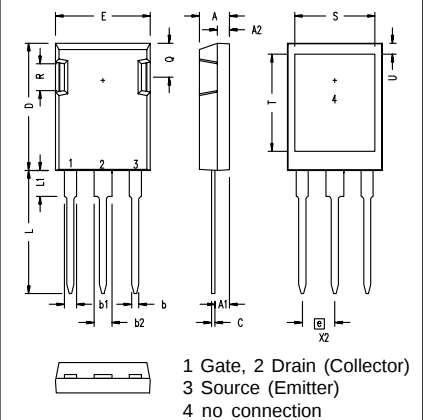
Symbol	Test Conditions		Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
			min.	typ.	max.
g_{fs}	$V_{DS} = 15\text{ V}; I_D = I_T$	Note 1	11	21	S
C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$			4200	pF
C_{oss}				450	pF
C_{rss}				135	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = I_T$ $R_G = 1\ \Omega$ (External),			16	25 ns
t_r				33	45 ns
$t_{d(off)}$				65	80 ns
t_f				30	40 ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = I_T$			135	160 nC
Q_{gs}				28	40 nC
Q_{gd}				62	85 nC
R_{thJC}					0.50 K/W
R_{thCK}				0.15	K/W

Source-Drain Diode

Source-Drain Diode		Characteristic Values (T _J = 25°C, unless otherwise specified)			
Symbol	Test Conditions	min.	typ.	max.	
I _S	V _{GS} = 0 V			26	A
I _{SM}	Repetitive; pulse width limited by T _{JM}			104	A
V _{SD}	I _F = I _S , V _{GS} = 0 V, Note 1			1.5	V
t _{rr}	I_F = I_S, -di/dt = 100 A/μs, V_R = 100 V	T _J = 25°C	1 2	250	ns
Q _{RM}		T _J = 125°C		400	ns
		T _J = 25°C		1.5	μC
		T _J = 125°C			μC
I _{RM}		T _J = 25°C		10	A
	T _J = 125°C	15	A		

Note: 1. Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$
 2. I_T test current: IXFR26N50 $I_T = 13\text{ A}$
 IXFR24N50 $I_T = 12\text{ A}$
 3. See IXFR26N50 data sheet for characteristic curves.

ISOPLUS 247 (IXFR) OUTLINE



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	.190	.205
A ₁	2.29	2.54	.090	.100
A ₂	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b ₁	1.91	2.13	.075	.084
b ₂	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	.244
R	4.32	4.83	.170	.190
S	13.21	13.72	.520	.540
T	15.75	16.26	.620	.640
U	1.65	3.03	.065	.080